

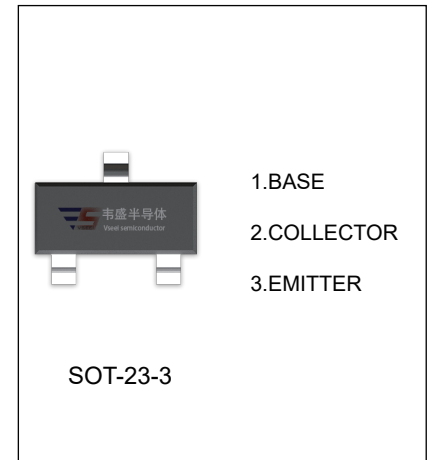
FMMT619 TRANSISTOR (NPN)

FEATURE

- Low Saturation Voltage

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	2	A
P_C	Power Dissipation	0.35	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	357	$^\circ\text{C}/\text{W}$
P_{CM}	Maximum Power Dissipation (note 1)	0.625	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient (note 1)	200	$^\circ\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	50			V
Collector-emitter breakdown voltage (note 2)	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=40\text{V}, I_E=0$			100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			100	nA
DC current gain (note 2)	$h_{FE(1)}$	$V_{CE}=2\text{V}, I_C=10\text{mA}$	200			
	$h_{FE(2)}$	$V_{CE}=2\text{V}, I_C=0.2\text{A}$	300			
	$h_{FE(3)}$	$V_{CE}=2\text{V}, I_C=1\text{A}$	200			
	$h_{FE(4)}$	$V_{CE}=2\text{V}, I_C=2\text{A}$	100			
	$h_{FE(5)}$	$V_{CE}=2\text{V}, I_C=6\text{A}$		40		
Collector-emitter saturation voltage (note 2)	$V_{CE(sat)1}$	$I_C=0.1\text{A}, I_B=10\text{mA}$			20	mV
	$V_{CE(sat)2}$	$I_C=1\text{A}, I_B=10\text{mA}$			200	mV
	$V_{CE(sat)3}$	$I_C=2\text{A}, I_B=100\text{mA}$			220	mV
Base-emitter saturation voltage (note 2)	$V_{BE(sat)}$	$I_C=2\text{A}, I_B=50\text{mA}$			1	V
Base-emitter on voltage (note 2)	$V_{BE(on)}$	$I_C=2\text{A}, V_{CE}=2\text{V}$			1	V
Output capacitance	C_{ob}	$V_{CB}=10\text{V}, f=1\text{MHz}$			20	pF
Turn-on time	$t_{(on)}$	$V_{CC}=10\text{V}, I_C=1\text{A}, I_{B1}=-I_{B2}=10\text{mA}$		170		ns
Turn-off time	$t_{(off)}$			750		ns
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=50\text{mA}, f=100\text{MHz}$	100			MHz

Notes :

1. Maximum power dissipation is calculated assuming that the device is mounted on a ceramic substrate measuring 15x15x0.6mm.
2. Pulse test: Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2.0\%$.

